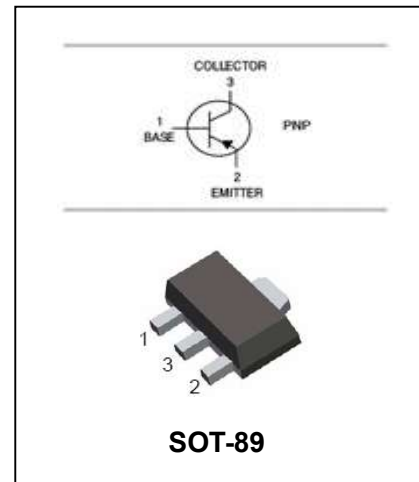


PNP Silicon AF Transistors

BCX69

FEATURES

- For general AF applications.
- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.
- Complementary type:BCX68.



ORDERING INFORMATION

Type No.	Marking	Package Code
BCX69	CE	SOT-89
BCX69-10	CF	SOT-89
BCX69-16	CG	SOT-89
BCX69-25	CH	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-25	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1	A
I _{CM}	Collector Current -Peak	-2	A
I _B	Base Current	-0.1	A
I _{BM}	Peak Base Current	-0.2	A
P _D	Total Power Dissipation	1	W
T _j , T _{stg}	Junction and Storage Temperature	-65 to +150	°C

PNP Silicon AF Transistors

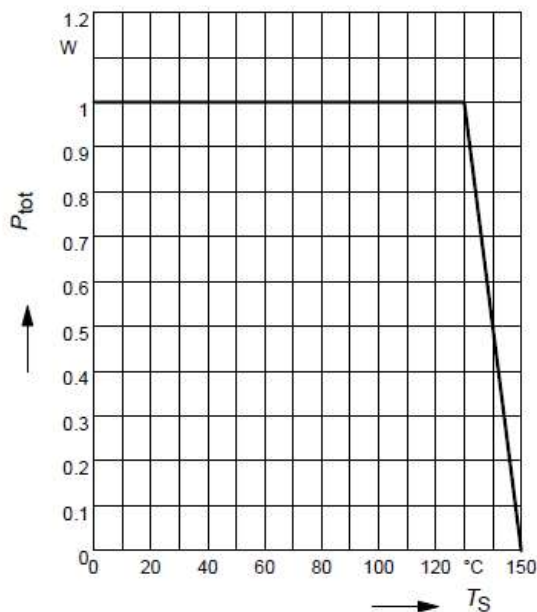
BCX69

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-25		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -30mA, I_B = 0$	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\mu A, I_C = 0$	-5		μV
Collector cut-off current	I_{CBO}	$V_{CB} = -25V, I_E = 0$		-100	nA
		$V_{CB} = -25V, I_E = 0, T_A = 150^\circ C$		-100	μA
DC current gain	h_{FE}	$V_{CE} = -10V, I_C = -5mA$	50		
		$V_{CE} = -1V, I_C = -500mA$	85	375	
		BCX69-10	85	160	
		BCX69-16	100	250	
		$V_{CE} = -1V, I_C = -1A$	60		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -100mA$		-0.5	V
Base-emitter voltage	V_{BE}	$I_C = -1A, V_{CE} = -1V$		-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -100mA,$ $f = 20MHz$	100		MHz

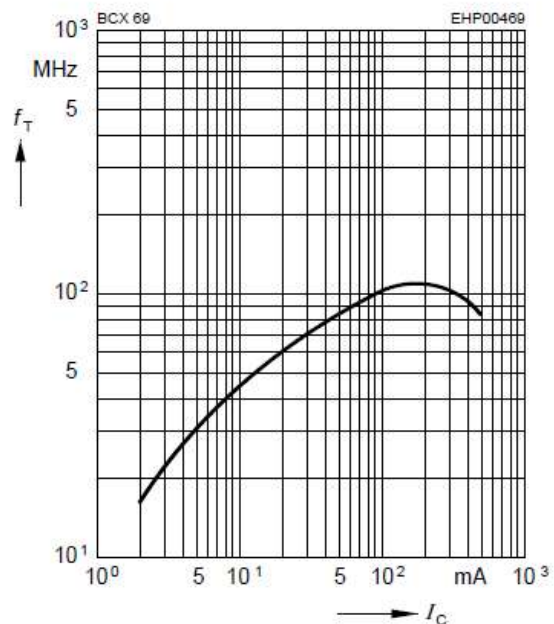
TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Total power dissipation $P_{tot} = f(T_S)$



Transition frequency $f_T = f(I_C)$

$V_{CE} = 5V$

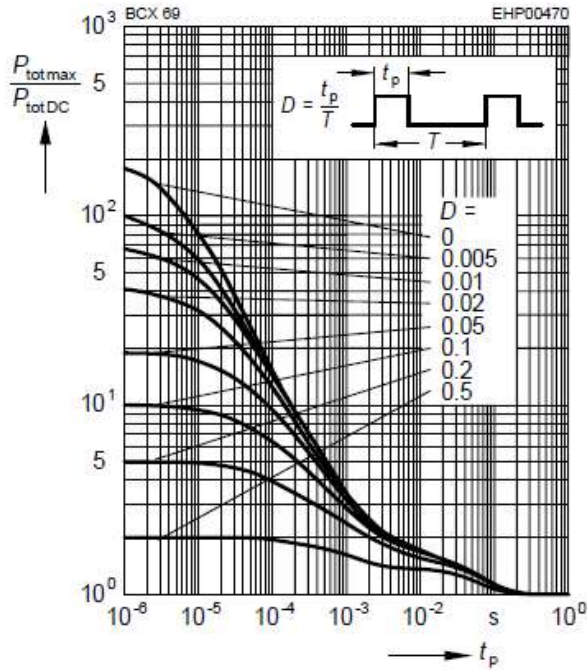


PNP Silicon AF Transistors

BCX69

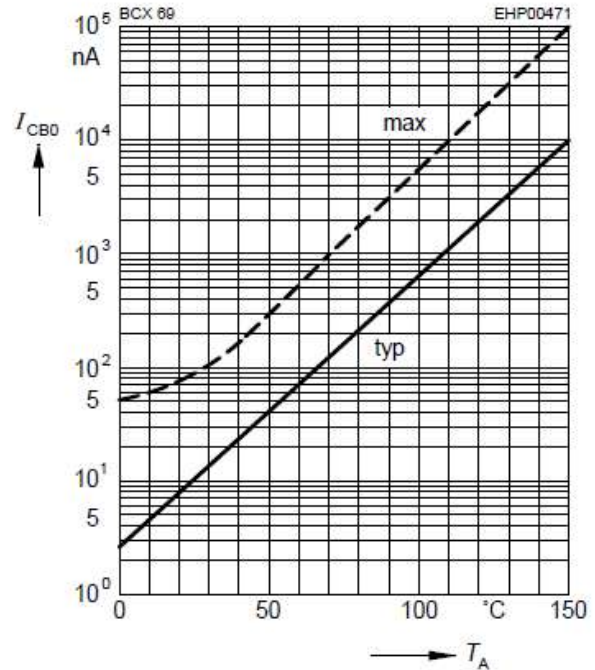
Permissible pulse load

$$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$$



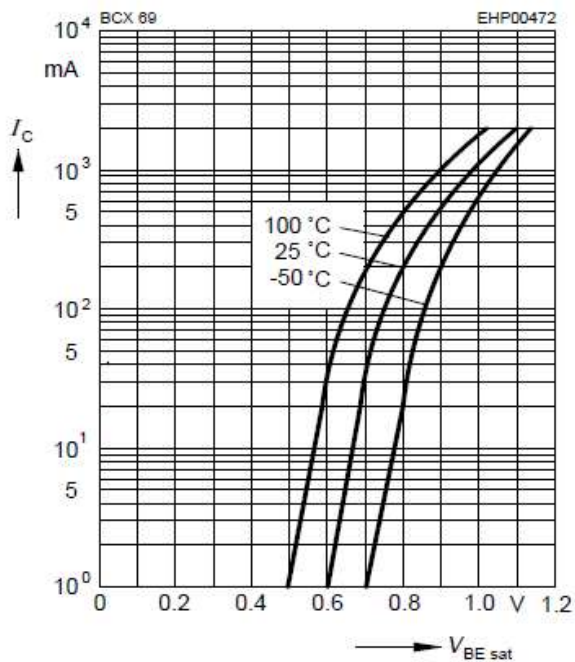
Collector cutoff current $I_{\text{CBO}} = f(T_A)$

$$V_{\text{CB}} = 25\text{V}$$



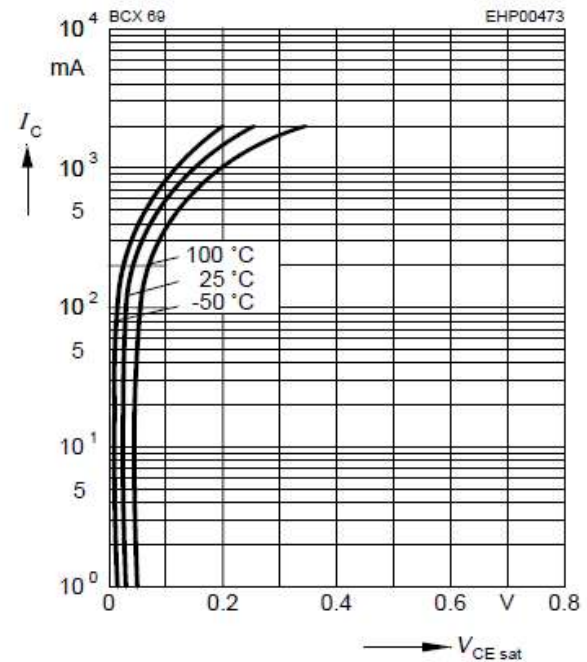
Base-emitter saturation voltage

$$I_C = f(V_{\text{BEsat}}), h_{\text{FE}} = 10$$



Collector-emitter saturation voltage

$$I_C = f(V_{\text{CEsat}}), h_{\text{FE}} = 10$$



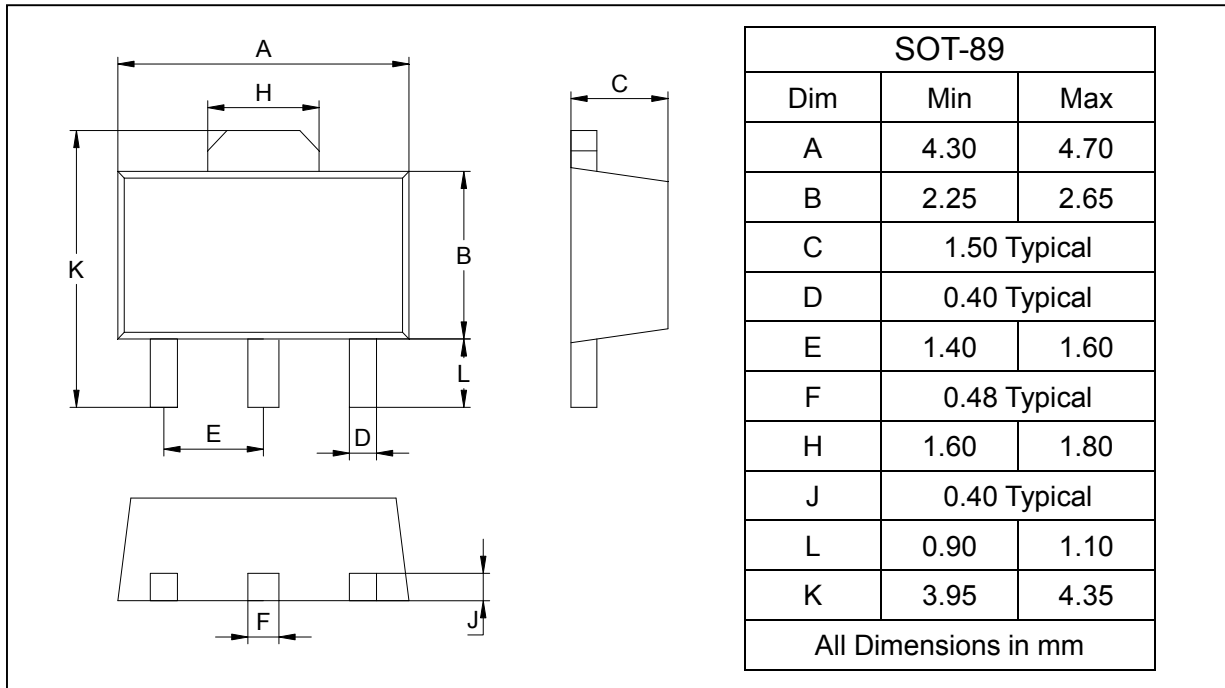
PNP Silicon AF Transistors

BCX69

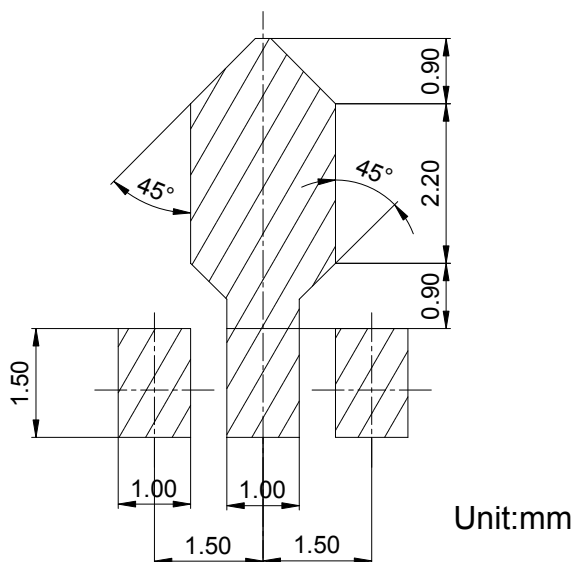
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BCX69	SOT-89	1000/Tape&Reel